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Data; 1.3.4.2. Parameters; 1.3.5. Limits of the distributional approach; 1.4. CAT software prototype for comparable corpora processing; 1.4.1. Implementation of a term alignment method; 1.4.1.1. Implementation and data; 1.4.1.2. Extraction of the terms to be aligned; 1.4.1.3. Collecting context vectors; 1.4.1.3.1. Monolexical term context vectors; 1.4.1.4. Polylexical term context vectors; 1.4.1.5. Translation of the source context vectors; 1.4.1.6. Term alignment; 1.4.2. Terminological records extraction 1.4.3. Lexicon consultation interface 1.5. Summary; Chapter 2: User-Centered Evaluation of Lexicons Extracted from Comparable Corpora; 2.1. Introduction; 2.2. Translation quality evaluation methodologies; 2.2.1. Machine translation evaluation; 2.2.1.1. Automatic evaluation measures; 2.2.1.2. Human MT evaluation; 2.2.2. Human translation evaluation; 2.2.2.1. Quantitative models; 2.2.2.2. Non-quantitative models; 2.2.3. Discussion; 2.3. Design and experimentation of a user-centered evaluation; 2.3.1. Methodological aspects; 2.3.1.1. Evaluation criteria and purpose 2.3.1.2. Subject matter expertise 2.3.1.3. Basis for comparison; 2.3.2. Experimentation protocol; 2.3.2.1. Data; 2.3.2.1.1. Comparable corpora and extracted lexica; 2.3.2.1.2. Texts to be translated; 2.3.2.1.3. Resources used in the translation situation; 2.3.2.1.4. Translators and judges; 2.3.2.2. Evaluation progress; 2.3.2.2.1. Translation phase; 2.3.2.2.2. Translation quality evaluation phase; 2.3.3. Results; 2.3.3.1. Lexicons usability; 2.3.3.1.1. Translation speed; 2.3.3.1.2. Use of resources; 2.3.3.1.3. Translators' impressions on the lexicons extracted from comparable corpora 2.3.3.2. Quality of the generated translations

Sommario/riassunto

Computer-assisted translation (CAT) has always used translation memories, which require the translator to have a corpus of previous translations that the CAT software can use to generate bilingual lexicons. This can be problematic when the translator does not have such a corpus, for instance, when the text belongs to an emerging field. To solve this issue, CAT research has looked into the leveraging of comparable corpora, i.e. a set of texts, in two or more languages, which deal with the same topic but are not translations of one another. This work had two primary objectives. The first is to

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	Titolo	Die Gotter - Vorstellungen uber den Kosmos - Der Untergang des Heidentums / von Jan de Vries
	Pubbl/distr/stampa	Berlin : Walter de Gruyter, 1970
	Edizione	[3., unveranderte Auflage]
	Descrizione fisica	492 p. ; 23 cm
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3.	Record Nr.	UNINA9910830878003321
	Autore	Enz Christian
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	Pubbl/distr/stampa	Chichester, England ; ; Hoboken, NJ, : John Wiley, c2006
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Charge-based MOS Transistor Modeling; Contents; Foreword; Preface; List of Symbols; 1 Introduction; 1.1 The Importance of Device Modeling for IC Design; 1.2 A Short History of the EKV MOS Transistor Model; 1.3 The Book Structure; Part I The Basic Long-Channel Intrinsic Charge-Based Model; 2 Definitions; 2.1 The N-channel Transistor Structure; 2.2 Definition of Charges, Current, Potential, and Electric Fields; 2.3 Transistor Symbol and P-Channel Transistor; 3 The Basic Charge Model; 3.1 Poisson's Equation and Gradual Channel Approximation; 3.2 Surface Potential as a Function of Gate Voltage; 3.3 Gate Capacitance; 3.4 Charge Sheet Approximation; 3.5 Density of Mobile Inverted Charge; 3.5.1 Mobile Charge as a Function of Gate Voltage and Surface Potential; 3.5.2 Mobile Charge as a Function of Channel Voltage and Surface Potential; 3.6 Charge-Potential Linearization; 3.6.1 Linearization of $Q_i(s)$; 3.6.2 Linearized Bulk Depletion Charge Q_b ; 3.6.3 Strong Inversion Approximation; 3.6.4 Evaluation of the Slope Factor; 3.6.5 Compact Model Parameters; 4 Static Drain Current; 4.1 Drain Current Expression; 4.2 Forward and Reverse Current Components; 4.3 Modes of Operation; 4.4 Model of Drain Current Based on Charge Linearization; 4.4.1 Expression Valid for All Levels of Inversion; 4.4.2 Compact Model Parameters; 4.4.3 Inversion Coefficient; 4.4.4 Approximation of the Drain Current in Strong Inversion; 4.4.5 Approximation of the Drain Current in Weak Inversion; 4.4.6 Alternative Continuous Models; 4.5 Fundamental Property: Validity and Application; 4.5.1 Generalization of Drain Current Expression; 4.5.2 Domain of Validity; 4.5.3 Causes of Degradation; 4.5.4 Concept of Pseudo-Resistor; 4.6 Channel Length Modulation; 4.6.1 Effective Channel Length; 4.6.2 Weak Inversion; 4.6.3 Strong Inversion; 4.6.4 Geometrical Effects; 5 The Small-Signal Model; 5.1 The Static Small-Signal Model; 5.1.1 Transconductances; 5.1.2 Residual Output Conductance in Saturation; 5.1.3 Equivalent Circuit; 5.1.4 The Normalized Transconductance to Drain Current Ratio; 5.2 A General NQS Small-Signal Model; 5.3 The QS Dynamic Small-Signal Model; 5.3.1 Intrinsic Capacitances; 5.3.2 Transcapacitances; 5.3.3 Complete QS Circuit; 5.3.4 Domains of Validity of the Different Models; 6 The Noise Model; 6.1 Noise Calculation Methods; 6.1.1 General Expression; 6.1.2 Long-Channel Simplification; 6.2 Low-Frequency Channel Thermal Noise; 6.2.1 Drain Current Thermal Noise PSD; 6.2.2 Thermal Noise Excess Factor Definitions; 6.2.3 Circuit Examples; 6.3 Flicker Noise; 6.3.1 Carrier Number Fluctuations (Mc Wörther Model); 6.3.2 Mobility Fluctuations (Hooge Model); 6.3.3 Additional Contributions Due to the Source and Drain Access Resistances; 6.3.4 Total $1/f$ Noise at the Drain; 6.3.5 Scaling Properties; 6.4 Appendices; Appendix: The Nyquist and Bode Theorems; Appendix: General Noise Expression; 7 Temperature Effects and Matching; 7.1 Introduction; 7.2 Temperature Effects

Modern, large-scale analog integrated circuits (ICs) are essentially composed of metal-oxide semiconductor (MOS) transistors and their interconnections. As technology scales down to deep sub-micron dimensions and supply voltage decreases to reduce power consumption, these complex analog circuits are even more dependent on the exact behavior of each transistor. High-performance analog circuit design requires a very detailed model of the transistor, describing accurately its static and dynamic behaviors, its noise and matching limitations and its temperature variations. The charge-based EKV (Enz